Revision. 1

MOS FET

FJ4B01100L

Panasonic

FJ4B01100L

Single P-channel MOS FET

For Load switching circuits

■ Features

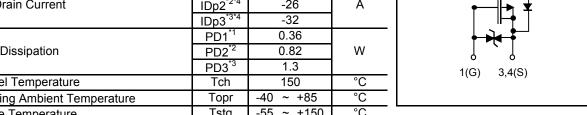
- Low Drain-source ON resistance:Rds(on) typ. = 68 m Ω (VGS = -2.5 V)
- · CSP (Chip Size Package)
- · RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 1D

■ Packaging

Embossed type (Thermo-compression sealing): 20 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

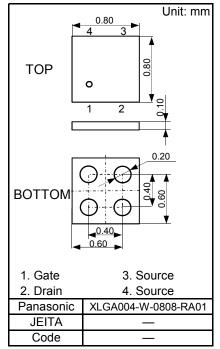
Parameter	Symbol	Rating	Unit			
Drain-Source Voltage	VDS	-12	V			
Gate-Source Voltage	VGS	±8	V			
	ID1 ^{*1}	-2.2				
Drain Current	ID2*2	-3.3	Α			
	ID3 ^{*3}	-4.1				
Peak Drain Current	IDp1*1*4	-17	Α			
	IDp2*2*4	-26				
	IDp3 ^{*3*4}	-32				
	PD1 ^{*1}	0.36	W			
Power Dissipation	PD2 ^{*2}	0.82				
	PD3 ^{*3}	1.3				
Channel Temperature	Tch	150	°C			
Operating Ambient Temperature	Topr	-40 ~ +85	°C			
Storage Temperature	Tstg	-55 ~ +150	°C			
2						

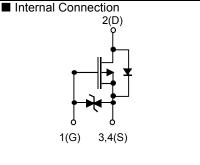


- Note *1 FR4 board (25.4mm×25.4mm×t1.0mm), Min Cu 36mm² Copper
 - *2 FR4 board (25.4mm×25.4mm×t1.0mm), Full Cu
 - *3 Ceramic substrate (70mm×70mm×t1.0mm)
 - *4 $t = 10 \mu s$, Duty Cycle < 1%

Established: 2014-03-27

Revised





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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0	-12			V
Zero Gate Voltage Drain Current	IDSS	VDS = -12 V, VGS = 0			-10	μA
Gate-Source Leakage Current	IGSS	VGS = ±8 V, VDS = 0 V			±10	μA
Gate Threshold Voltage	Vth	ID = -1.2 mA, VDS =-10 V	-0.3		-1.0	V
Drain-Source ON Resistance	RDS(on)	ID = -1.5 A, VGS = -4.5 V		57	74	m()
		ID = -1.5 A, VGS = -2.5 V		68	90	
		ID = -0.2 A, VGS = -1.8 V		82	139	mΩ
		ID = -0.1 A, VGS = -1.5 V		97	290	
Input Capacitance *1	Ciss	VDS = -10 V		459		
Output Capacitance *1	Coss	VGS = 0		85		pF
Reverse Transfer Capacitance *1	Crss	f = 1MHz		75		
Turn-on delay time *1,*2	td(on)	VDD = -6 V		8		
Rise time *1,*2	tr	VGS = 0 to -4.5 V		11		ns
Turn-off delay time *1,*2	td(off)	ID = -1.0 A		59		
Fall time *1,*2	tf	1D = -1.0 A		10		
Total Gate Charge *1	Qg	VDD = -6 V		7		nC
Gate to Source Charge *1	Qgs	VGS = -4.5 V		0.75		nC
Gate to Drain Miller Charge *1	Qgd	ID = -1.0 A		0.95		nC
Body Diode Forward Voltage	VF(D-S)	IF = -0.2A, VGS = 0V		-0.7	-1.2	V

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

■ Electrical State Discharge Characteristics

Standard	Test Type	Symbol	Conditions	Class	Value	Unit
AEC-Q101-001	Human body model	HBM	C = 100 pF, R = $1.5 \text{ k}\Omega$	H1C	>1k to ≦ 2k	V
	Machine model	MM	C = 200 pF, R = 0 Ω	M2	>100 to \leq 200	V

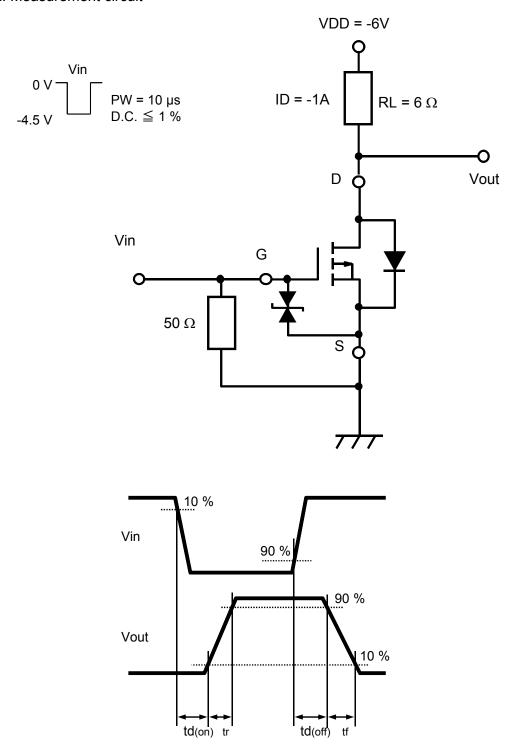
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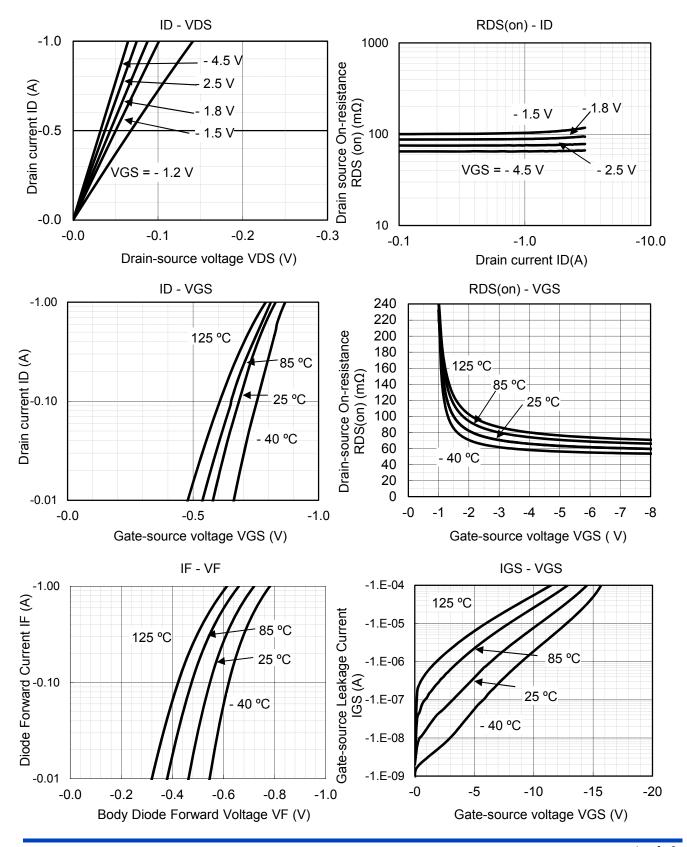
^{*1} Guaranteed by design, not subject to production testing

^{*2} Measurement circuit for Turn-on delay time / Rise time / Turn-off delay time / Fall time

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Note2: Measurement circuit

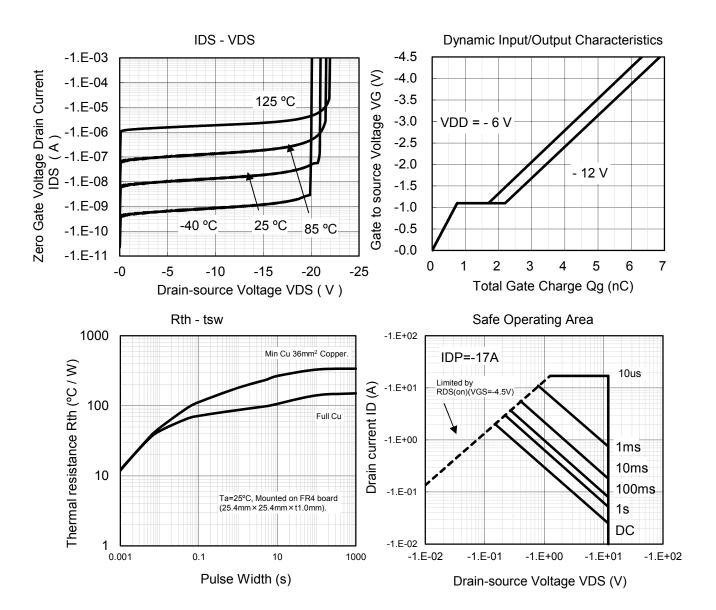




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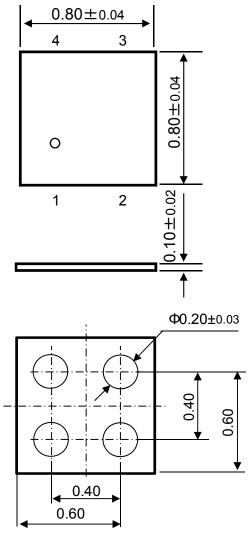


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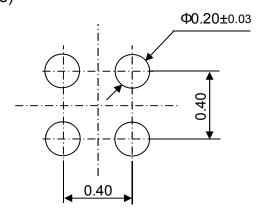
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■ XLGA004-W-0808-RA01

Unit: mm



■ Land Pattern (Reference)



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